

COMMON EMITTER AMPLIFIER

VOLTAGE DIVIDER CIRCUIT

LOAD POINT CALCULATIONS

Given:

| Quantity | Description | Value |
|----------|------------------------------|--------------|
| Vcc | Dc Supply voltage | 15V |
| Ic | Capacitor current at Q-point | 3mA |
| B \ Hfe | Current Gain | 200 (2N2222) |
| Vbe | Bias-Emitter Voltage | 0.7V |

Practical Assumptions:

| Quantity | Formula | Substitutions | Value |
|----------|-------------------|---------------|-------|
| Vre | 10% of Vcc | $0.1 * 15$ | 1.5V |
| Vrc | 40% of Vcc | $0.4 * 15$ | 6V |
| Vceq | 50% of Vcc | $0.5 * 15$ | 7.5V |
| Vce | $V_{cc} - V_{rc}$ | $15 - 6$ | 9V |

Terminal Resistances:

| Quantity | Formula | Substitutions | Value |
|----------|----------------------------------|---------------|---------------|
| Ie | $\sim I_c$ | | 3mA |
| Re | $V_{re} / I_e \sim V_{re} / I_c$ | $1.5 / 3m$ | 0.5k Ω |
| Rc | V_{rc} / I_c | $6 / 3m$ | 2k Ω |

Base Terminal & Divider calculations:

| Quantity | Formula | Substitutions | Value |
|----------|-------------------|---------------|-------|
| Vb | $V_{re} + V_{be}$ | $1.5 + 0.7$ | 2.2V |
| Ib | I_c / B | $3m / 200$ | 15uA |

| | | | |
|------------------|----------------------------|-----------------------|-----------------|
| I _{div} | $10 \cdot I_b$ | $10 \cdot 15\mu$ | 150 μ A |
| R _{b1} | $(V_{cc} - V_b) / I_{div}$ | $(15 - 2.2) / 150\mu$ | 85.33k Ω |
| R _{b2} | V_b / I_{div} | $2.2 / 150\mu$ | 14.67k Ω |

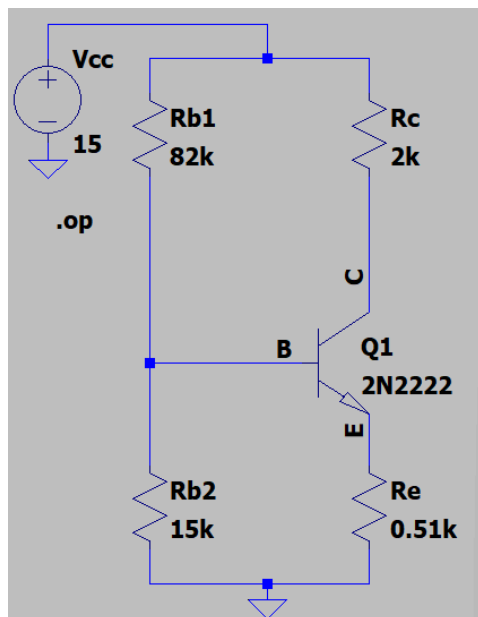
Swapping calculated resistor values to closest E24 series resistors (offers 5% tolerance)

| Quantity | Original | Closes Standard value | Change (%) |
|-----------------|----------|-----------------------|------------|
| R _e | 500 | 510 | 2 |
| R _c | 2k | 2k | 0 |
| R _{b1} | 85.33k | 82k | 3.9 |
| R _{b2} | 14.67k | 15k | 2.25 |

Expected Q point shift:

| Quantity | Formula | Substitutions | Value |
|---------------------------------|---|--------------------------------|--------------|
| R _b | $R_{b1} + R_{b2}$ | $82k + 15k$ | 97k Ω |
| V _b | $V_{cc} \cdot [R_{b2} / (R_{b1} + R_{b2})]$ | $15 \cdot [15k / (82k + 15k)]$ | 2.32V |
| I _e ~ I _c | $(V_b - V_{be}) / R_e$ | $(2.32 - 0.7) / 510$ | 3.18mA |

Results:



--- Operating Point ---

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V(b) :      2.14862      voltage
V(c) :      9.27352      voltage
V(e) :      1.46713      voltage
V(n001) :    15          voltage
I(Rb1) :     0.000156724  device_current
I(Rb2) :     0.000143241  device_current
I(Rc) :      0.00286324   device_current
I(Re) :      0.00287672   device_current
I(Vcc) :     -0.00301996  device_current
Ib(Q1) :     1.34832e-05  device_current
Ic(Q1) :     0.00286324   device_current
Ie(Q1) :     -0.00287672  device_current
Is(Q1) :      0          device_current

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Based on assumptions made above, an error of 10-15% is permissible.

| Quantity | Calculated | Simulated | Absolute Difference | Error % |
|----------|------------|-------------------------------|---------------------|---------|
| Vb | 2.32 | 2.14862 | 0.17138 | 7.39 |
| Vc | 9 | 9.27352 | 0.27352 | 3.04 |
| Ve | 1.5 | 1.46713 | 0.03287 | 2.19 |
| Vce | 7.5 | $9.57937 - 1.36151 = 7.80639$ | 0.30639 | 4.01 |

AC PARAMETERS CALCULATIONS

| Quantity | Description | Calculations | Value |
|--|--|---|-----------------------|
| Dynamic emitter resistance ($r_{e'}$) | Thermal Voltage / Collector current | $V_t / I_c = 25\text{mV} / 3.18\text{mA}$ | 7.86Ω |
| AC base resistance [$R_{in}(\text{base})$] | Resistance of the emitter circuit "reflected" to the base by the current gain. | $B * r_{e'} = 200 * 7.86$ | $1.572\text{k}\Omega$ |
| Input Impedance | The parallel combination of the two base-biasing resistors (R_{b1} & R_{b2}) and the AC resistance looking into the base $R_{in}(\text{base})$. | $R_{b1} \parallel R_{b2} \parallel R_{in}(\text{base}) = 82\text{k} \parallel 15\text{k} \parallel 1.572\text{k}$ | $1.398\text{k}\Omega$ |
| Output Impedance | $\sim R_c$ | | $2\text{k}\Omega$ |
| Ideal Voltage Gain (A_v) [emitter resistor bypassed] | Gain produced in output voltage | $-R_c / r_{e'} = -2\text{k} / 7.86$ | -254.45 |
| Coupling Capacitors | High-pass filters, setting the low-frequency cutoff (f_L) | $C = 1 / (2 * \pi * f_c * R)$ | $f_c = 20\text{Hz}$ |
| Input resistance (R_{in}) | | $R_s (\text{source series resistance}) + Z_{in} = 50 + 1.398$ | $1.448\text{k}\Omega$ |

| | | | |
|----------------------------------|---|--|-----------------------|
| Input coupling Capacitor (Cin) | | $1/(2\pi R_{in} f_c) = 1/(2\pi \cdot 1.448 \cdot 20)$ | 22uF |
| Output coupling Capacitor (Cout) | | $1/(2\pi (R_I + Z_{out}) f_c) = 1/(2\pi (1k + 2k) \cdot 20)$ | 10.6uF ~ 10uF or 15uF |
| Emitter Bypass Capacitor (Ce) | Ce is also a high-pass filter that determines a low-frequency cutoff (fce). It must be large enough so that its reactance is much smaller than Re at the lowest operating frequency (fL). | $R_{seen} \approx r_e' + (R_{b1} + R_{b2}) / \beta = 7.86 + 12.86k / 200 = 71.26\Omega$ $C_e = 1 / (2\pi f_c R_{seen}) = 1/(2\pi \cdot 5 \times 71.26)$ | 446uF ~ 470uF |

Expected Results:

| Quantity | Description | Calculations | Value |
|---|---|--|-------------|
| AC Collector Resistance (rc) | | $R_c \parallel R_I = 2k \parallel 1k$ | 0.667kΩ |
| Actual Loaded Gain [Av (loaded)] (without Ce) | Emitter resistor unbypassed | $-r_c / (r_e' + R_e) = -667 / (7.86 + 510)$ | -1.288 |
| Actual Loaded Gain [Av (loaded)] (with Ce) | Emitter resistor bypassed | $-r_c / r_e' = 667 / 7.86$ | -84.86 |
| Maximum Output Swing (ΔVout): | Minimum of distance from cutoff and saturation region | Saturation: $V_{ce} - V_{ce(sat)} = 7.5 - 0.2 = 7.3V$ Cutoff: $V_{cc} - V_{ce} = 15 - 7.5 = 7.5V$ | 7.3V (peak) |
| Maximum Input Voltage [Vin (peak)] | | $\Delta V_{out} / A_v (loaded) = 7.3 / 84.86$ | 86mV |

NOTE: With given parameters the Vin (peak) which can be amplified without distortion is ~5mV. This is due to the non-linear characteristic of the BJT's base-emitter junction (the re' resistance) which becomes very pronounced when the emitter is bypassed.

A general rule of thumb for BJT amplifiers to remain in the linear small-signal region is that the AC emitter current i_e must be small enough that the AC voltage across r_e' is much less than the thermal voltage, V_t :

$$V_e = i_e * r_e' \ll V_t (25\text{mV})$$

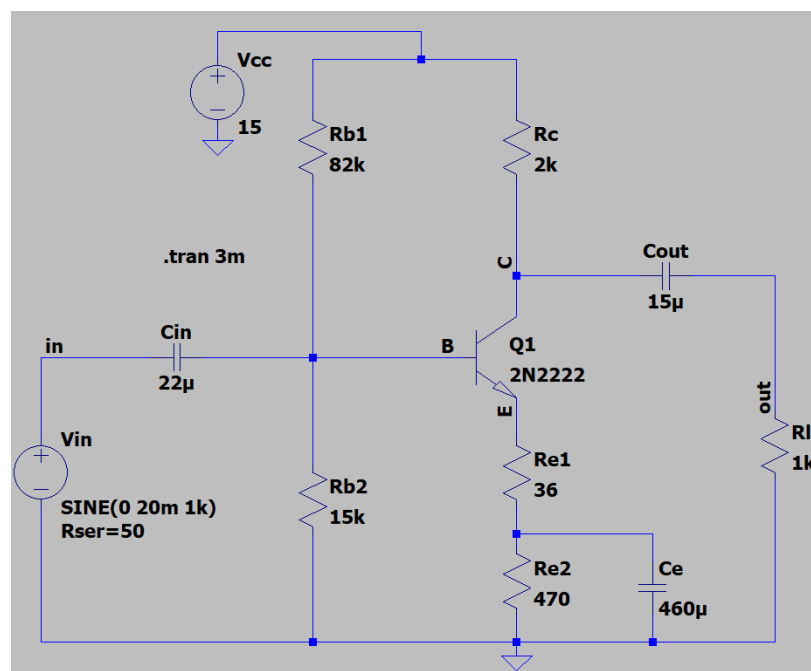
Since $v_{in} \sim v_{be} = v_e$

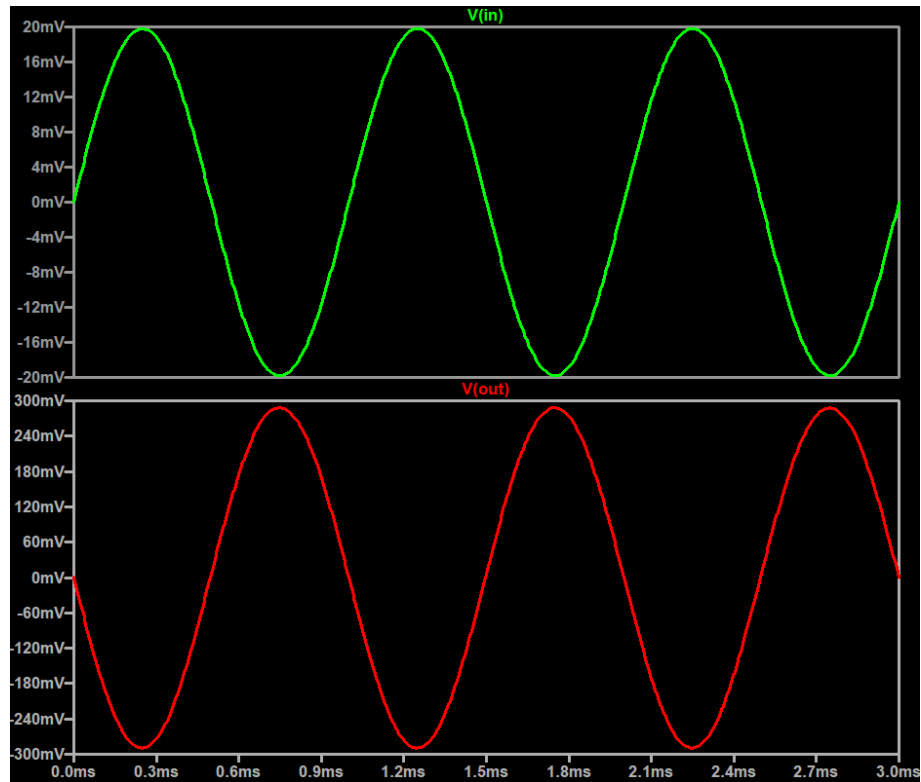
$$V_{in(\text{peak})} \ll 25\text{mV}$$

Typically, the limit for acceptable distortion in a fully bypassed CE stage is around 5mV to 10mV peak.

Ac negative feedback:

| Quantity | Description | Calculations | Value |
|-----------------------|---|--|----------------------|
| $V_{in(\text{peak})}$ | New permissible input peak voltage | | 50mV |
| $A_{v(\text{new})}$ | More realistic gain for better linearity | | -15 |
| R_{e1} | unbypassed to provide AC feedback and linearity | $A_v(\text{new}) = -r_c / (r_e' + R_{e1})$ $\Rightarrow R_{e1} = -r_c / A_{v(\text{new})} - r_e' = 667 / 15 - 7.86$ | $36.6 \sim 36\Omega$ |
| R_{e2} | Bypassed by C_e for DC stability | $R_e - R_{e1} = 510 - 36$ | $474 \sim 470\Omega$ |





FREQUENCY RESPONSE ANALYSIS

Low Frequency Analysis

| Quantity | Description | Calculations | Value |
|--|---------------------------|---|----------------|
| Transistor's base resistance (Rin(base)) | | $B \cdot (r_e' + R_{e1}) = 200 \cdot (7.86 + 300)$ | 8.77k Ω |
| Input Impedance (Zin) | | $R_{b1} \parallel R_{b2} \parallel R_{in}(\text{base}) = 82k \parallel 15k \parallel 8.77k$ | 5.18k Ω |
| fc (in) | | $1 / (2 \cdot \pi \cdot C_{in} \cdot (Z_{in} + R_s)) = 1 / (2 \cdot \pi \cdot 22 \cdot 10^{-6} \cdot (5180 + 50))$ | 1.39Hz |
| fc (out) | | $1 / (2 \cdot \pi \cdot C_{out} \cdot (Z_{out} + R_l)) = 1 / (2 \cdot \pi \cdot 15 \cdot 10^{-6} \cdot (2k + 1k))$ | 3.54Hz |
| Rseen | The resistance seen by Ce | $R_{e2} \parallel (r_e' + (R_{b1} \parallel R_{b2} \parallel R_s) / (B + 1)) = 470 \parallel (7.86 + (82k \parallel 15k \parallel 50) \cdot (200 + 1))$ | 8 Ω |

| | | | |
|-----------------|----------------------|--|---------|
| f _{ce} | | $1 / (2\pi \cdot C_e \cdot R_{seen}) = 1 / (2\pi \cdot 460 \cdot 10^{-6} \cdot 8)$ | *43.3Hz |
| f _L | low-frequency cutoff | *max(f _c (in), f _c (out)) | 3.54Hz |

*Calculated f_{ce} is very high and should be close to f_c (in) and f_c (out) and therefore ignored

High frequency analysis

High-frequency cutoff is determined by the parasitic capacitances within the transistor and any stray wiring capacitance. These capacitances act as low-pass filters.

| Quantity | Description | Calculations | Value |
|---------------------------------------|---|--|---------|
| C _{be} | Base emitter capacitance, effects the input | 2N2222 | 25pF |
| C _{bc} | Base collector capacitance, effects both input and output due to the Miller effect. | 2N2222 | 8pF |
| C _{millar} (C _m) | | $C_{bc} \cdot (1 - A_v) = 8p \cdot (1 - (-15))$ | 128pF |
| C _{in} (total) | | $C_{be} + C_m = 25p + 128p$ | 153pF |
| R _{th} | | $R_s \parallel R_{b1} \parallel R_{b2} = 50 \parallel 82k \parallel 15k$ | 50 |
| f _H | high-frequency cutoff | $1 / (2\pi \cdot R_{th} \cdot C_{in}(total)) = 1 / (2\pi \cdot 50 \cdot 153p)$ | 20.8Mhz |

Expected Results:

| Quantity | Description | Calculations | Value |
|---------------------------|--|---------------------|------------------|
| Gain (db) | | $20 \cdot \log(15)$ | 23.5dB |
| Midband Range | | | 3.54Hz - 20.8MHz |
| Midband Phase | -180° across the midband | | |
| Low-Frequency Phase Shift | In high-pass filters the output voltage leads the input current as the frequency drops | | -90° |
| High-Frequency | In a low-pass filter, the | | -270° |

| | | | |
|-------------|--|--|--|
| Phase Shift | output voltage lags the input voltage. | | |
|-------------|--|--|--|

